

I. Allowable Subject Matter

The Examiner has indicated that Claims 14 and 15 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims. While the Applicants do not agree with the Examiner that independent Claim 9 does not include allowable subject matter, in an effort to expedite the prosecution of the present application, and for no other reason, the Applicants have amended the elements of dependent Claim 14 into independent Claim 9. Accordingly, the Applicants request the Examiner to remove all §102 and §103 rejections and pass Claims 9-12 and 15-17 to allowance.

II. Conclusion

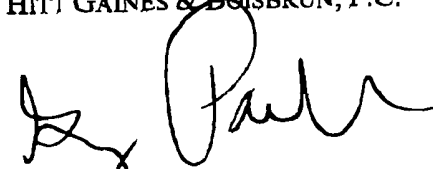
In view of the foregoing amendment and remarks, the Applicants now see all of the Claims currently pending in this application to be in condition for allowance and therefore earnestly solicit a Notice of Allowance for Claims 9-12 and 15-17.

Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. The attached page is captioned "Version with markings to show changes made."

The Applicants request the Examiner to telephone the undersigned attorney of record at (972) 480-8800 if such would further or expedite the prosecution of the present application.

Respectfully submitted,

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

(1) Kindly amend Claim 9 as follows:

9. (Twice Amended) A method of manufacturing ~~an~~ a semiconductor device, comprising:

creating a semiconductor substrate; and

forming an active region over the semiconductor substrate; and

forming an indium doped dielectric layer over ~~the semiconductor substrate~~ at least a portion of the active region, wherein ~~said~~ the indium doped dielectric layer has an indium concentration ranging from about 1 mole weight percent to about 15 mole weight percent.

(2) Kindly cancel Claim 14 without prejudice or disclaimer.

(3) Kindly amend Claim 15 as follows:

15. (Amended) The method as recited in Claim ~~14~~ 9 wherein forming an indium doped dielectric layer includes forming an indium doped dielectric layer using a manufacturing process selected from the group consisting of a physical vapor deposition process or a chemical vapor deposition process.